



#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-30V	5Ω @ V <sub>GS</sub> = -4.5V	
	6Ω @ V <sub>GS</sub> = -2.5V	-0.2A
	7Ω @ V <sub>GS</sub> = -1.8V	-U.ZA
	10Ω @ V <sub>GS</sub> = -1.5V	

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- **Power Management Functions**
- **Analog Switch**





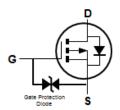


## **Features and Benefits**

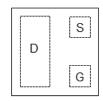
- Low Package Profile, 0.42mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, -1.0V Max
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Weight: 0.001 grams (Approximate)







Top View Package Pin Configuration

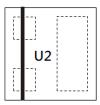
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP32D9UFZ-7B	X2-DFN0606-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



Top View Bar Denotes Gate and Source Side

U2 = Product Type Marking Code

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# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±10	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-200 -100	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-700	mA		

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P <sub>D</sub>	390	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	322	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

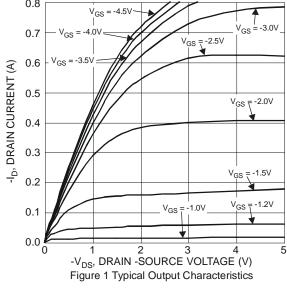
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

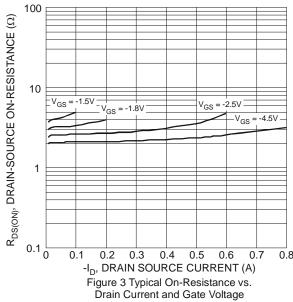
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						100t Condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	) I <sub>DSS</sub>	_	_	-100	nA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>		_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	•		•	•		•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	_	5	Ω	$V_{GS} = -4.5V, I_D = -100mA$	
		_	_	6		$V_{GS} = -2.5V, I_D = -50mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	7		$V_{GS} = -1.8V, I_D = -20mA$	
		1	_	10		$V_{GS} = -1.5V, I_D = -10mA$	
		_	6	_		$V_{GS} = -1.2V, I_D = -1mA$	
Diode Forward Voltage		_	-0.75	-1.0	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	1	22.5	_	pF		
Output Capacitance		1	2.9	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.1	_	pF	-1 = 1.UIVIDZ	
Total Gate Charge	Qg	_	0.35	_	nC	45777	
Gate-Source Charge	Qgs	_	0.06	_	nC	$V_{GS} = -4.5V, V_{DS} = -5V,$ $I_{D} = -200 \text{mA}$	
Gate-Drain Charge	$Q_{gd}$	_	0.09	_	nC	110 = -200MA	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.1	_	ns		
Turn-On Rise Time	t <sub>R</sub>		2.3	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	19.9	_	ns	$R_G = 6\Omega$ , $I_D = -200$ mA	
Turn-Off Fall Time	t <sub>F</sub>	_	10.5	_	ns		

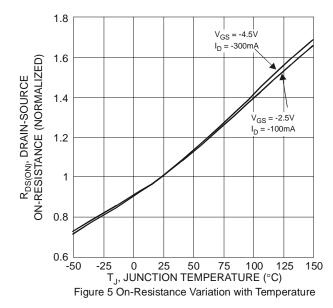
Notes:

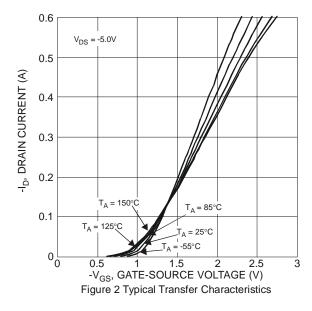
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

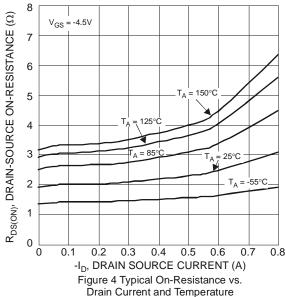


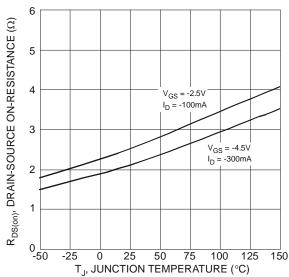
















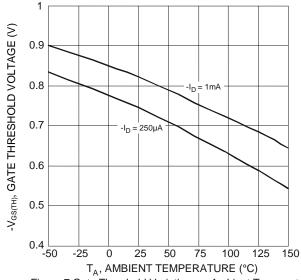
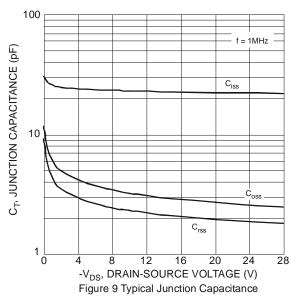
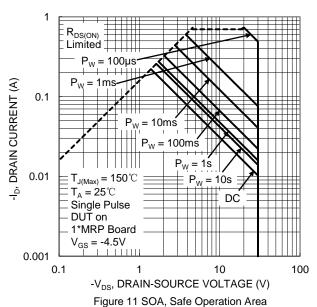
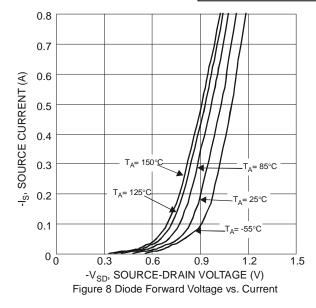
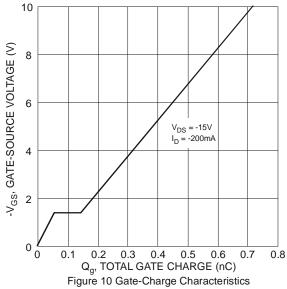


Figure 7 Gate Threshold Variation vs. Ambient Temperature











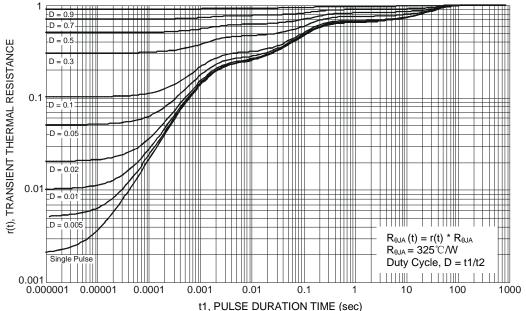


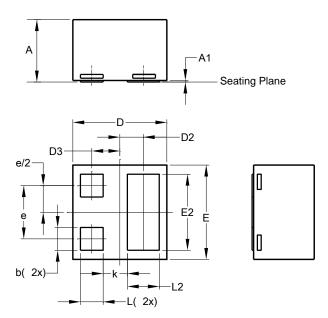
Figure 12 Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN0606-3

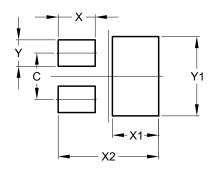


X2-DFN0606-3					
Dim	Min	Max	Тур		
Α	0.36	0.42	0.39		
A1	0	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57	0.67	0.62		
D2	0.155 BSC				
D3	0	0.185 BSC			
Е	0.57	0.67	0.62		
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
L	0.09	0.21	0.15		
L2	0.11	0.31	0.21		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN0606-3



Dimensions	Value (in mm)		
С	0.350		
Х	0.280		
X1	0.350		
X2	0.760		
Y	0.200		
Y1	0.600		



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